

### Features

- Freq: 2~8GHz
- Isolation: 16dB
- Insertion Loss: 1dB
- Chip Size: 1.13mm×0.88mm×0.1mm

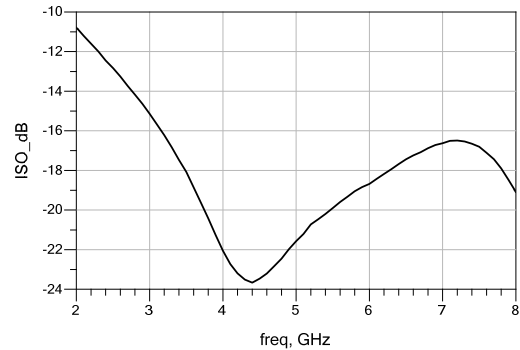
### General Description

The HG125GA is a 2-way GaAs pHEMT power divider that is operating from 2 to 8 GHz. This chip features very high isolation of 16 dB and extremely low insertion loss of 1 dB. Input and output VSWR are 1.4/1.4.

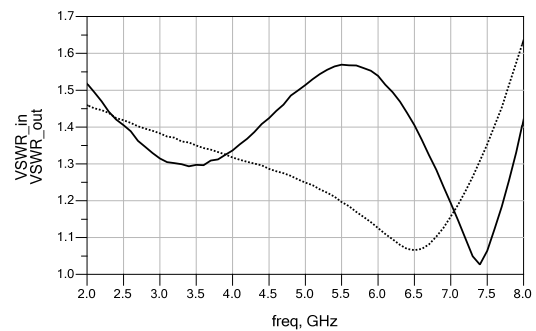
### Electrical Specifications (T<sub>A</sub>=25 °C)

Parameter	Min.	Typ.	Max.
Frequency Range(GHz)	2~8		
Input VSWR	-	1.4	-
Output VSWR	-	1.4	-
Insertion Loss(dB)	-	1	-
Isolation (dB)	-	16	-

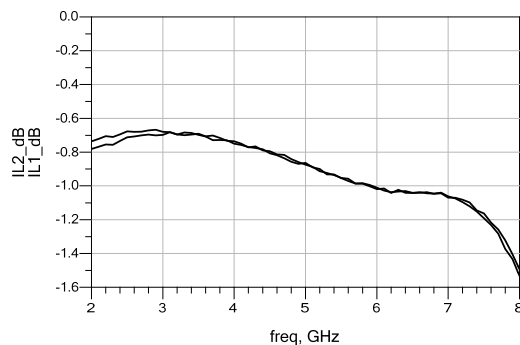
### Isolation



### Input and Output VSWR



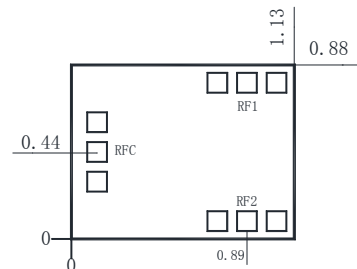
### Insertion Loss



### Absolute Maximum Ratings

RF Input Power	+27dBm
Operating Temperature	-55°C~125°C
Storage Temperature	-65°C~150°C

### Outline Drawing (mm)



### Notes:

- The chip should be stored in a dry and nitrogen environment, and used in a clean environment.
- GaAs material is brittle, can not touch the surface of the chip, must be careful when using.
- The chip is welding with conductive adhesive or alloy (alloy temperature should not exceed 300°C, and no more than 30 sec. ), and should make it fully grounded.
- The chip microwave port and substrate gap is not exceeding 0.05mm, with Φ25μm double gold wire bonding, suggested length of gold wire 250~400μm.
- Chip microwave port without DC blocking capacitor.
- The chip is sensitive to static electricity, and should be protected against static electricity during storage and use.